

In the claims:

Please substitute the following full listing of claims for the claims as originally filed or most recently amended.

1. (Currently Amended) A field effect transistor formed at a surface of a layer of semiconductor material, said field effect transistor comprising
a gate structure formed on said surface of said layer of semiconductor material, and
a discontinuous film of material within said layer of semiconductor material and having a discontinuity aligned to said gate structure wherein said discontinuous film is a stressed film.
2. (Previously Presented) A field effect transistor as recited in claim 1, wherein said discontinuity is self-aligned to said gate structure.
3. (Canceled)
4. (Currently Amended) A field effect transistor as recited in claim 3 1, wherein said stressed film comprises an insulator.
5. (Canceled)